

•General Description

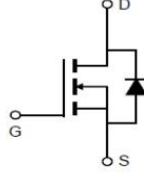
The SJ MOSFET LH65R260C has the low $R_{DS(on)}$, low gate charge, fast switching and excellent avalanche characteristics. This device offers extremely fast and robust body diode, and is suitable for telecom and power supplies.

•Features

- Much lower $R_{DS(on)}$ & Much lower Input Capacitance
- 100% EAS Guaranteed

•Application

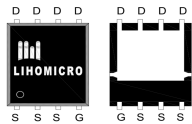
- LED/LCD/ TV and monitor Lighting
- UPS Inverter System
- Power Supplies



$V_{DS} = 650V$

$R_{DS(on)} = 260m\Omega$

$I_D = 15A$



■ RoHS COMPLIANT

DFN5*6

•Ordering Information:

Part number	LH65R260C
Package	DFN5*6
Basic ordering unit (pcs)	5000
Normal Package Material Ordering Code	LH65R260CN-DFN5*6-TAP
Halogen Free Ordering Code	LH65R260CN-DFN5*6-TAP-HF

•Absolute Maximum Ratings (TC = 25°C)

PARAMETER		SYMBOL	Value	UNIT
Drain-Source Breakdown Voltage		BV_{DSS}	650	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current	TC = 25°C	I_D	15	A
	TC = 100°C		9	
Pulsed drain current (TC = 25°C, tp limited by Tjmax) ¹		$I_D \text{ pulse}$	45	A
Single Pulse Avalanche Energy ¹		I_{AR}	7	A
Single Pulse Avalanche Energy ²		E_{AS}	290	mJ
Repetitive Avalanche Energy ¹		E_{AR}	0.44	mJ
Power Dissipation (TC=25°C)		P_D	32	W
Operating Temperature and Storage Temperature Range		T_J/T_{STG}	-55~+150	°C
MOSFET dv/dt ruggedness, $V_{DS}=0\sim480V$		dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\sim480V, I_{SD} \leq I_D$		dv/dt	15	V/ns

●Electronic Characteristics

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	650	--	--	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	--	4.0	V
Drain-source On Resistance ³	$R_{DS(ON)}$	$V_{GS}=10V, I_D=7.5A$	--	0.24	0.26	Ω
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=650V, V_{GS}=0V, T_J=25^\circ C$	--	--	1	μA
		$V_{DS}=650V, V_{GS}=0V, T_J=125^\circ C$	--	--	100	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V$	--	--	± 10	μA
Forward Transconductance ³	R_G	$f=1.0MHz$ open drain	--	--	8.3	Ω
Input Capacitance	C_{iss}	$V_{GS}=0V,$ $V_{DS}=400V$ $f=1.0MHz$	--	890	--	pF
Output Capacitance	C_{oss}		--	33	--	
Reverse transfer Capacitance	C_{rss}		--	5	--	
Turn -Off Delay Time	$T_d(off)$	$V_{DD}=400V,$ $I_D=15.0A$ $R_G=25\Omega$	--	85	--	ns
Turn-on delay time	$T_d(on)$		--	19	--	
Rise time	T_r		--	43	--	
Fall time	T_f		--	34	--	
Total Gate Charge	Q_g	$I_D=15A,$ $V_{DS}=520V$ $V_{GS}=10V$	--	25	---	nC
Gate-to-Source Charge	Q_{gs}		--	6.5	--	
Gate-to-Drain Charge	Q_{gd}		--	10.5	---	
Continuous Diode Forward Current	I_S		--	--	15.0	A
Pulsed Diode Forward Current	I_{SM}		--	--	45.0	A
Diode Forward Voltage	V_{SD}	$T_J=25^\circ C, I_S=15.0A$ $V_{GS}=0V$	--	0.7	1.2	V
Reverse Recovery Time	t_{rr}	$V_{RR}=400V,$ $I_f=I_S$ $di_F/dt=100A/\mu s$	--	340	--	ns
Reverse Recovery Charge	Q_{rr}		--	4.1	--	μC
Peak Reverse Recovery Current	I_{RRM}		--	24	--	A

●Thermal Characteristics

PARAMETER	SYMBOL	MAX	UNIT
Thermal Resistance Junction-case	R_{thJC}	3.9	$^\circ C/W$
Thermal Resistance Junction-ambient	R_{thJA}	62.5	$^\circ C/W$

Notes:

1.Repetitive Rating: Pulse width limited by maximum junction temperature.

2. $I_{AS}=7A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^\circ C$

3. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$

• **Typical Characteristics** $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

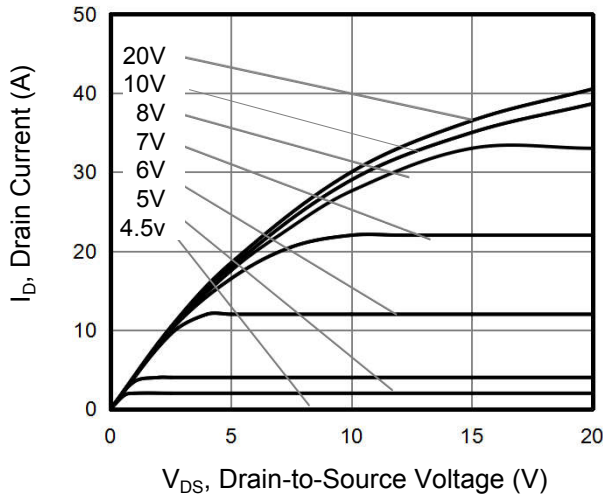


Figure 2. Transfer Characteristics

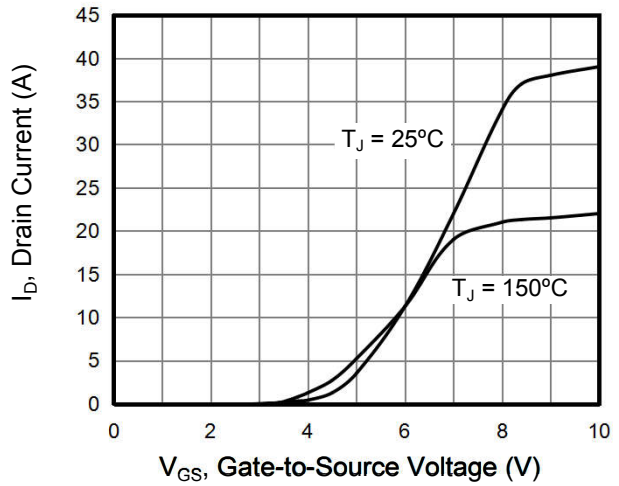


Figure 3. On-Resistance vs. Drain Current

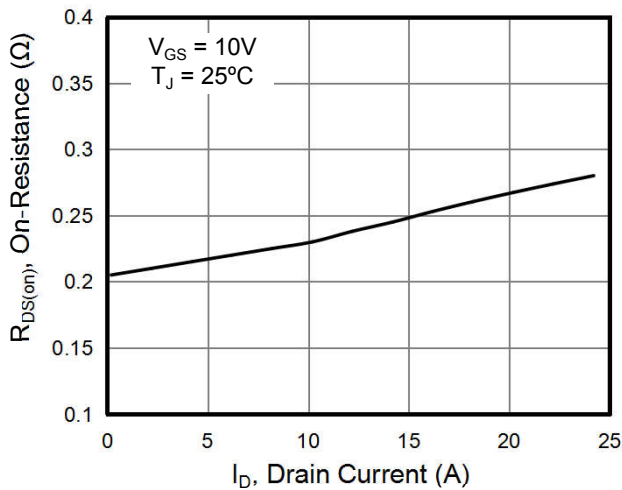


Figure 4. Capacitance

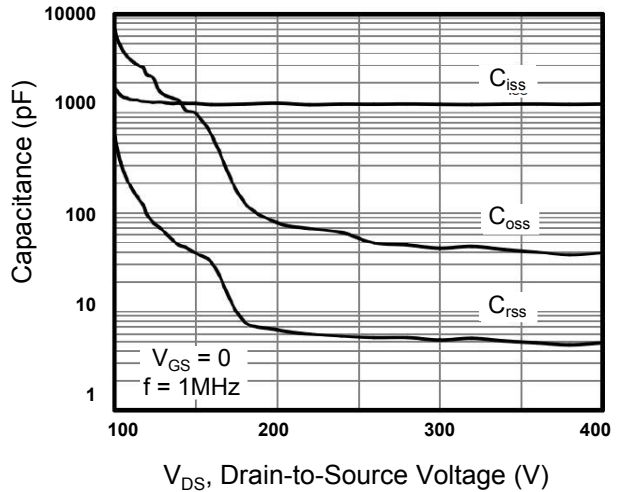


Figure 5. Gate Charge

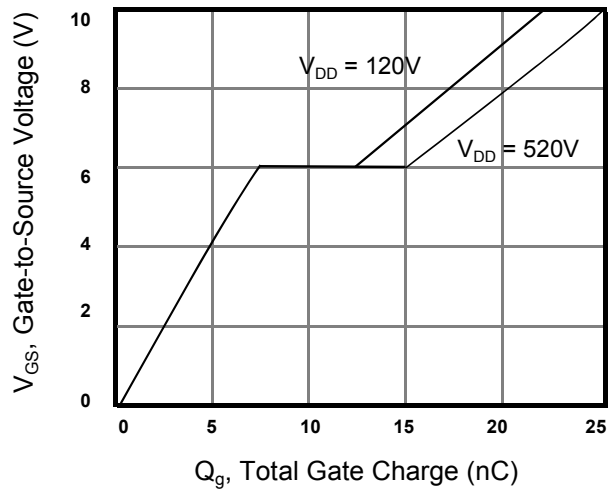
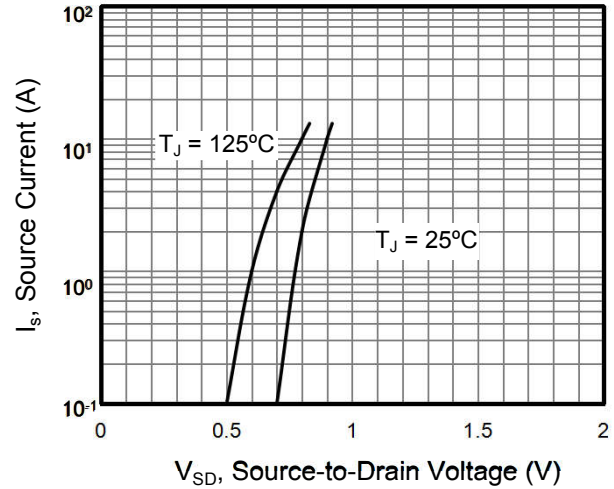


Figure 6. Body Diode Forward Voltage



● **Typical Characteristics**(cont.)

Figure 7. On-Resistance vs. Junction Temperature

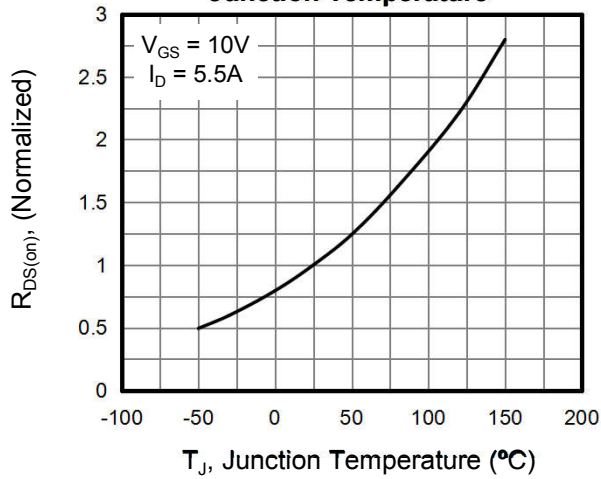


Figure 8. Threshold Voltage vs. Junction Temperature

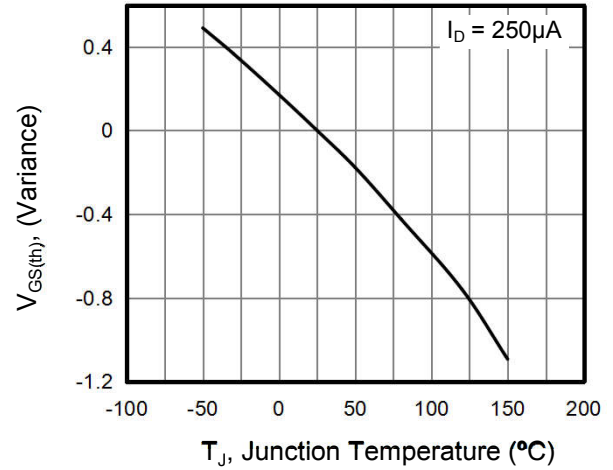


Figure 9. Breakdown voltage vs. Junction Temperature

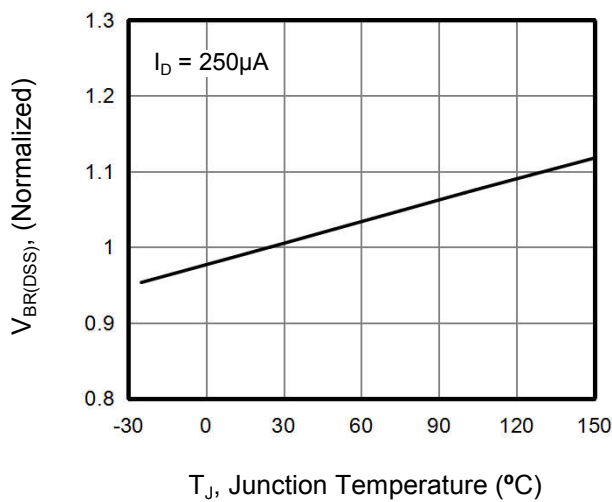


Figure 10. Transient Thermal Impedance

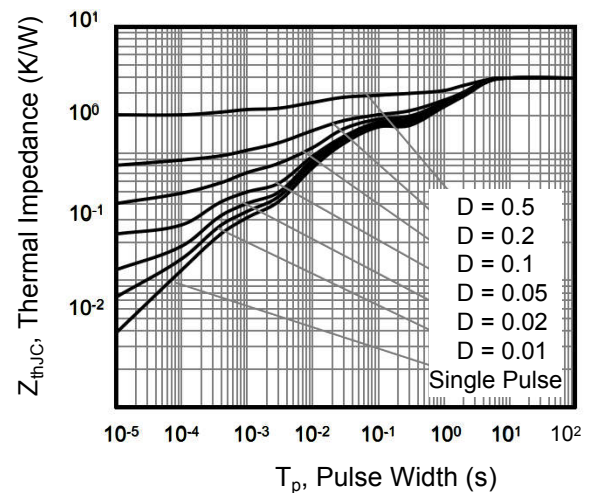
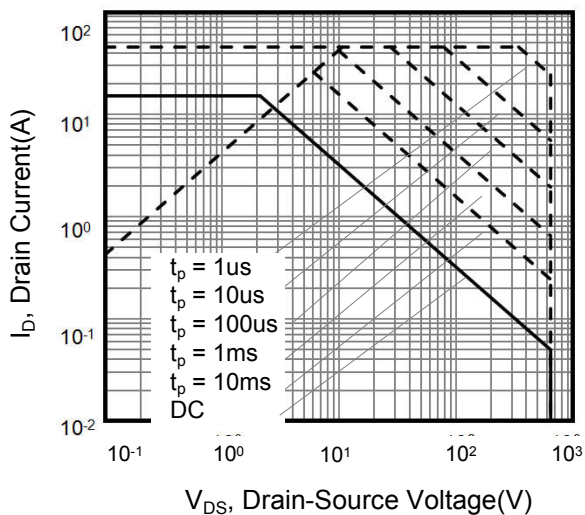


Figure 13. Safe operation area



• **Test Circuit and Waves**

Figure A: Gate Charge Test Circuit and Waveform

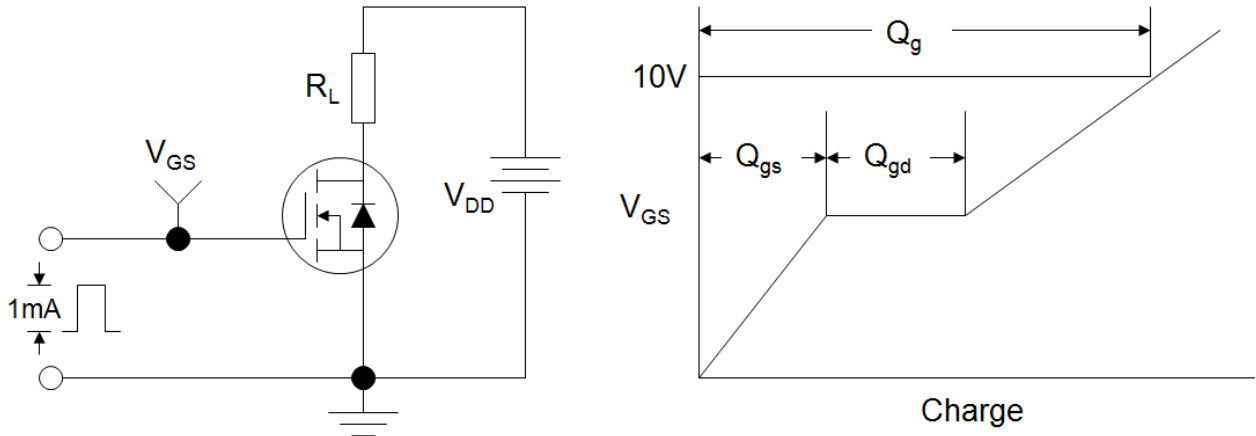


Figure B: Resistive Switching Test Circuit and Waveform

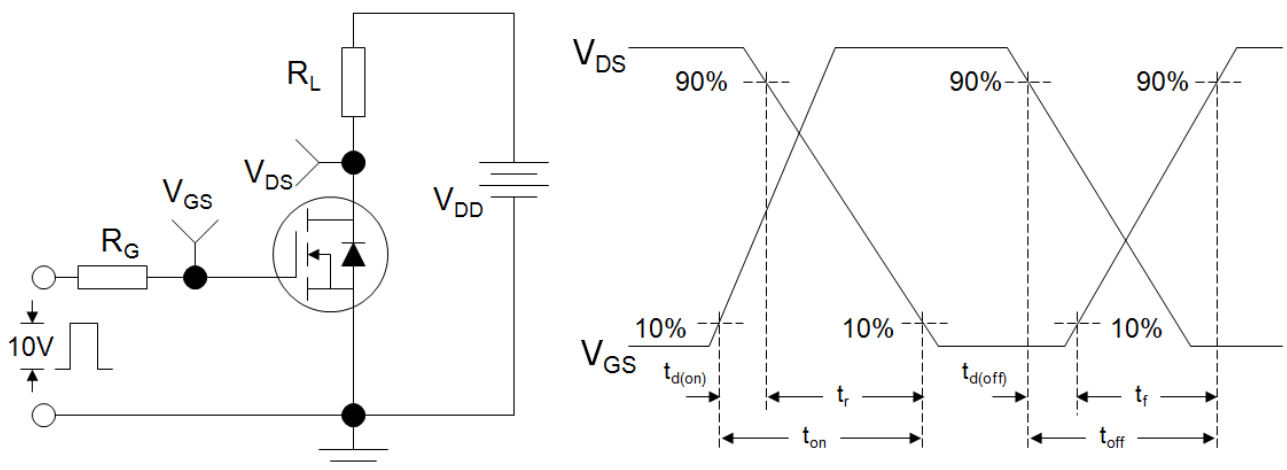
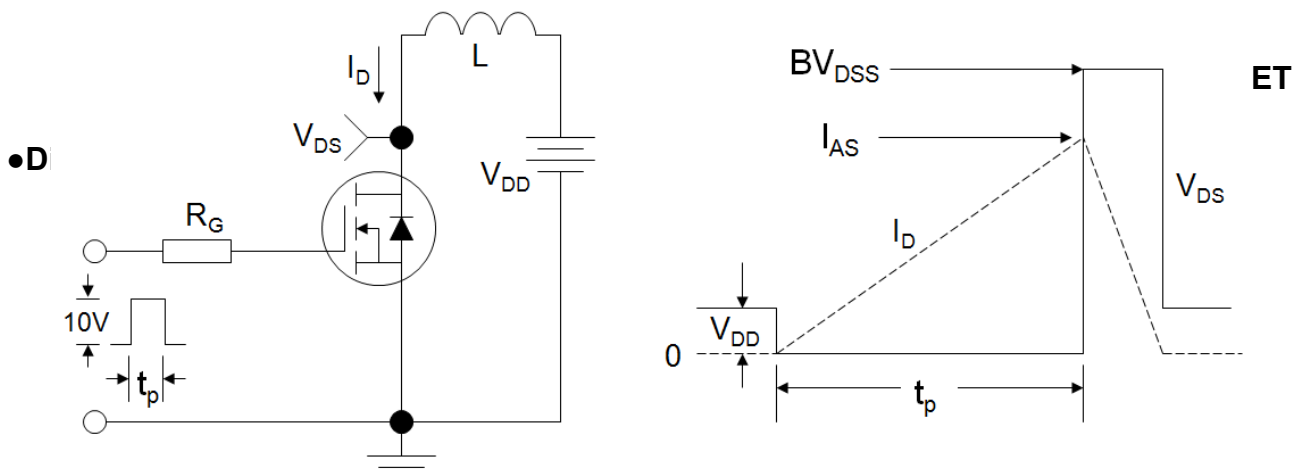


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



• **D**

●Dimensions (DFN5*6)

UNIT:mm

SYMBOL	min	max	SYMBOL	min	max
A	1.00	1.20	e	1.27BSC	
b	0.30	0.50	L	0.05	0.30
c	0.20	0.30	L1	0.40	0.80
D	4.80	5.20	L2	1.20	2.00
D1	3.90	4.30	H	3.30	3.80
E	5.50	5.90	I	—	0.18
E1	5.90	6.40			

